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RLT6505G TECHNICAL DATA

Visible Wavelength Laserdiode

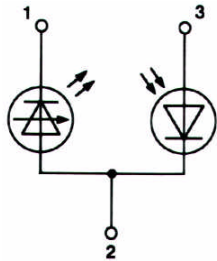
Structure: **AlGaInP**, index guided, single transverse mode

Lasing wavelength: **650 nm**

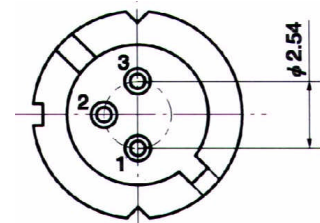
Max. optical power: **5 mW**

Package: **9 mm G or 5.6mm MG**

PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Maximum Ratings (T_c=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	5	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operation Case Temperature	T _C	-10 .. +40	°C
Storage Temperature	T _{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	kink free			5	mW
Threshold Current	I _{th}		20	30	40	mA
Operation Current	I _{op}	P _o =5mW		45	70	mA
Operating Voltage	V _{op}	P _o =5mW		2.2	2.7	V
Lasing Wavelength	λ _p	P _o =5mW		650	655	nm
Beam Divergence	q ₁	P _o =5mW	5	8	11	°
Beam Divergence	q ₂	P _o =5mW	25	31	37	°
Astigmatism	As	P _o =5mW, NA=0.4		11		μm
Monitor Current	I _m	P _o =5mW, V _r =5V		10		μA